L Number	Hits	Search Text	DB	Time stamp
1	44	5676587.pn. 5853604.uref. 5827781.uref.	USPAT; US-PGPUB	2004/04/27 17:04
2	10	5733177.uref.	USPAT; US-PGPUB	2004/04/27 17:07
3	21	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) same (relative near2 (speed velocity))	USPAT; US-PGPUB	2004/04/27 17:08
4	144	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))) and ((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))	USPAT; US-PGPUB	2004/04/27 17:10
5	9	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and (438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.)) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2004/04/27 17:16
6	34	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) same ((relative linear) near2 (speed velocity))	USPAT; US-PGPUB	2004/04/27 17:17
7	29	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) same ((rotat$6 near2 (speed velocity)) rpm rpms) same (change decreas$4 reduc$5)	USPAT; US-PGPUB	2004/04/27 17:21
8	4	(((cmp (chemical near mechanical)) with (copper cu conduct$4 metal))) and (relative near2 (speed velocity))	EPO; JPO; DERWENT; IBM_TDB	2004/04/27 17:22
9	127	(cmp (chemical near mechanical) polish$4) and ((carrier head) same (retain$4 ring) same membrane same (platen pad) same (pressure psi pa)) and (wafer substrate)	USPAT; US-PGPUB	2004/04/27 17:22
10	161	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp (chemical near mechanical) polish$4) with (copper cu conduct$4 metal)) and ((carrier head) same (retain$4 ring membrane) same (platen pad) same (pressure psi pa)) and (wafer substrate))	USPAT; US-PGPUB	2004/04/27 17:31
11	141	((cmp (chemical near mechanical) polish$4) and ((carrier head) same (retain$4 ring membrane)) and (platen pad)) and (pressure psi pa copper cu metal conduct$4)	EPO; JPO; DERWENT; IBM_TDB	2004/04/27 17:37
12	6	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same (rpm adj second))	USPAT; US-PGPUB	2004/04/27 17:40
13	0	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same ((rpm rotat$6) near accelerat$5))	USPAT; US-PGPUB	2004/04/27 17:41
14	2	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same ((rpm rotat$6) with accelerat$5))	USPAT; US-PGPUB	2004/04/27 17:41
15	30	(cmp (chemical near mechanical) polish$4) and (wafer substrate) and ((carrier head) same (platen pad) same accelerat$5)	USPAT; US-PGPUB	2004/04/27 17:41
16	519	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative near2 (speed velocity))	USPAT; US-PGPUB	2004/04/27 17:42
17	683	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp (chemical near mechanical) polish$4) and ((carrier head) same (retain$4 ring membrane)) and (wafer substrate) and (platen pad))	USPAT; US-PGPUB	2004/04/27 17:53